



Contribution ID: 277

Type: **Poster Presentation**

Characterization of dopant levels in a III-V molecular beam epitaxial system

Tuesday, 26 June 2018 15:00 (2 hours)

Commissioning of the III-V MBE system at the University of Pretoria has started. Doped GaAs layers have been grown and characterised electrically. The resulting carrier densities were used to determine the doping concentration versus cell temperature parameters that are required for controlled growth.

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Session Classification: Poster Session 1

Track Classification: Track A - Physics of Condensed Matter and Materials